NTHD5903T1

Power MOSFET
Dual P-Channel ChipFET™

2.1 Amps, 20 Volts

Features

- Low $R_{DS(on)}$ for Higher Efficiency
- Logic Level Gate Drive
- Miniature ChipFET Surface Mount Package Saves Board Space

Applications

- Power Management in Portable and Battery–Powered Products; i.e., Cellular and Cordless Telephones and PCMCIA Cards

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

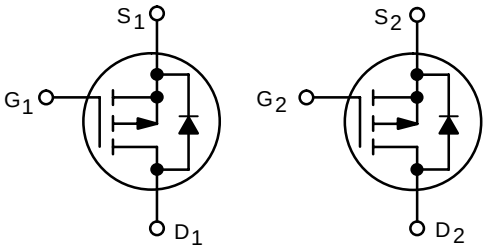
Rating	Symbol	5 secs	Steady State	Unit
Drain–Source Voltage	V_{DS}	–20		V
Gate–Source Voltage	V_{GS}	±12		V
Continuous Drain Current (T_J = 150°C) (Note 1) T_A = 25°C T_A = 85°C	I_D	 ±2.9 ±2.1	 ±2.1 ±1.5	A
Pulsed Drain Current	I_{DM}	±10		A
Continuous Source Current (Diode Conduction) (Note 1)	I_S	–1.8	–0.9	A
Maximum Power Dissipation (Note 1) T_A = 25°C T_A = 85°C	P_D	 2.1 1.1	 1.1 0.6	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150		°C

1. Surface Mounted on 1″ x 1″ FR4 Board.

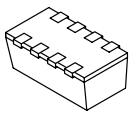
ON Semiconductor®

http://onsemi.com

DUAL P–CHANNEL
2.1 AMPS, 20 VOLTS
$R_{DS(on)}$ = 155 mΩ

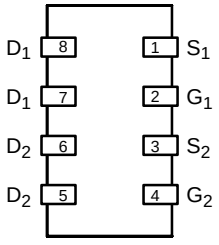


P–Channel MOSFET **P–Channel MOSFET**

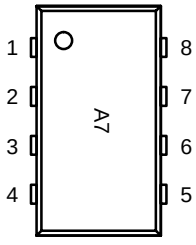


ChipFET
CASE 1206A
STYLE 2

PIN CONNECTIONS



MARKING DIAGRAM



A7 = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping
NTHD5903T1	ChipFET	3000/Tape & Reel

THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Maximum Junction–to–Ambient (Note 2) $t \leq 5$ sec Steady State	R_{thJA}	 50 90	 60 110	°C/W
Maximum Junction–to–Foot (Drain) Steady State	R_{thJF}	30	40	°C/W

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250$ μA	–0.6	–	–	V
Gate–Body Leakage	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = \pm 12$ V	–	–	±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -16$ V, $V_{GS} = 0$ V	–	–	–1.0	μA
		$V_{DS} = -16$ V, $V_{GS} = 0$ V, $T_J = 85$°C	–	–	–5.0	
On–State Drain Current (Note 3)	$I_{D(on)}$	$V_{DS} \leq -5.0$ V, $V_{GS} = -4.5$ V	–10	–	–	A
Drain–Source On–State Resistance (Note 3)	$r_{DS(on)}$	$V_{GS} = -4.5$ V, $I_D = -2.1$ A	–	0.130	0.155	Ω
		$V_{GS} = -3.6$ V, $I_D = -2.0$ A	–	0.150	0.180	
		$V_{GS} = -2.5$ V, $I_D = -1.7$ A	–	0.215	0.260	
Forward Transconductance (Note 3)	g_{fs}	$V_{DS} = -10$ V, $I_D = -2.1$ A	–	5.0	–	S
Diode Forward Voltage (Note 3)	V_{SD}	$I_S = -0.9$ A, $V_{GS} = 0$ V	–	–0.8	–1.2	V
Dynamic (Note 4)						
Total Gate Charge	Q_g	$V_{DS} = -10$ V, $V_{GS} = -4.5$ V, $I_D = -2.1$ A	–	3.0	6.0	nC
Gate–Source Charge	Q_{gs}		–	0.9	–	
Gate–Drain Charge	Q_{gd}		–	0.6	–	
Turn–On Delay Time	$t_{d(on)}$	$V_{DD} = -10$ V, $R_L = 10$ Ω, $I_D \cong -1.0$ A, $V_{GEN} = -4.5$ V, $R_G = 6$ Ω	–	13	20	ns
Rise Time	t_r		–	35	55	
Turn–Off Delay Time	$t_{d(off)}$		–	25	40	
Fall Time	t_f		–	25	40	
Source–Drain Reverse Recovery Time	t_{rr}	$I_F = -0.9$ A, di/dt = 100 A/μs	–	40	80	

2. Surface Mounted on 1″ x 1″ FR4 Board.
3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL CHARACTERISTICS

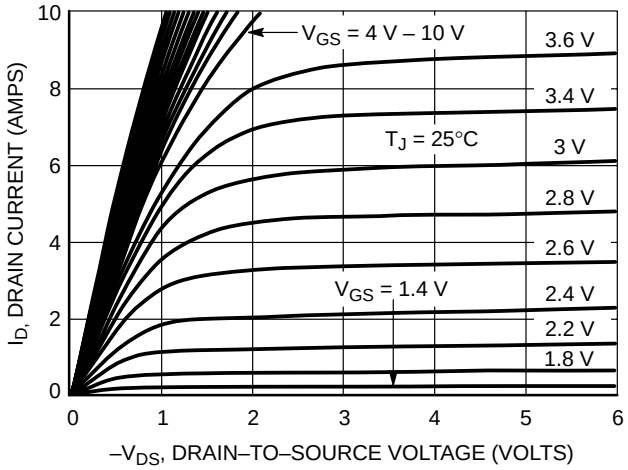


Figure 1. On–Region Characteristics

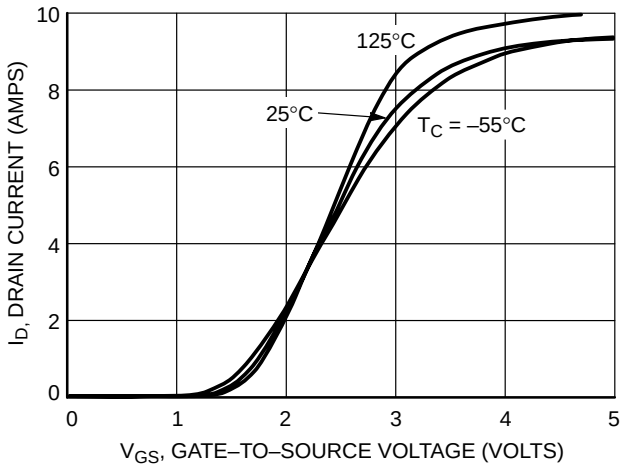


Figure 2. Transfer Characteristics

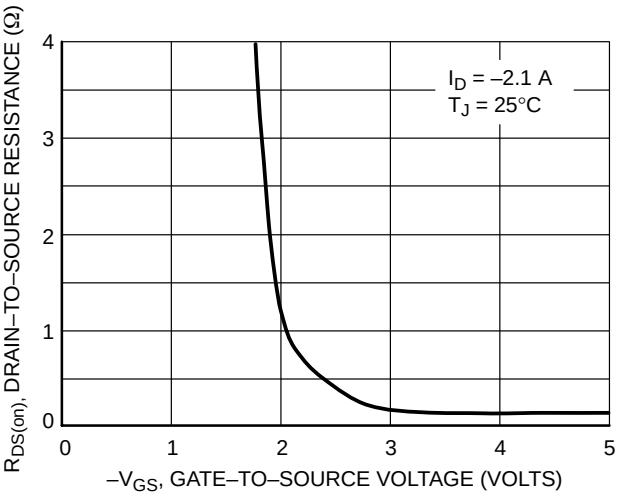


Figure 3. On–Resistance vs. Gate–to–Source Voltage

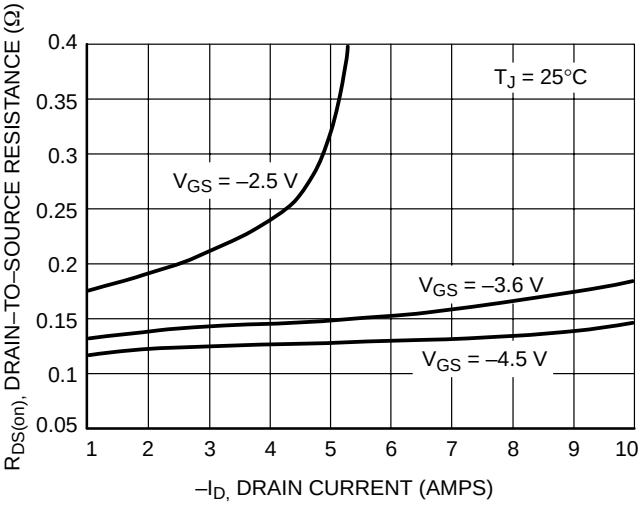


Figure 4. On–Resistance vs. Drain Current and Gate Voltage

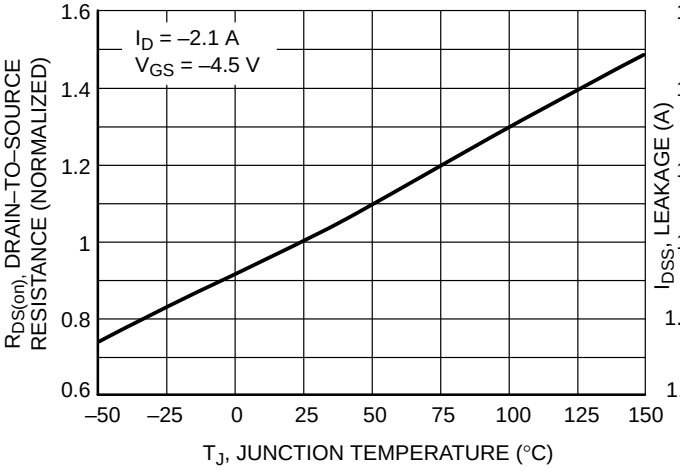


Figure 5. On–Resistance Variation with Temperature

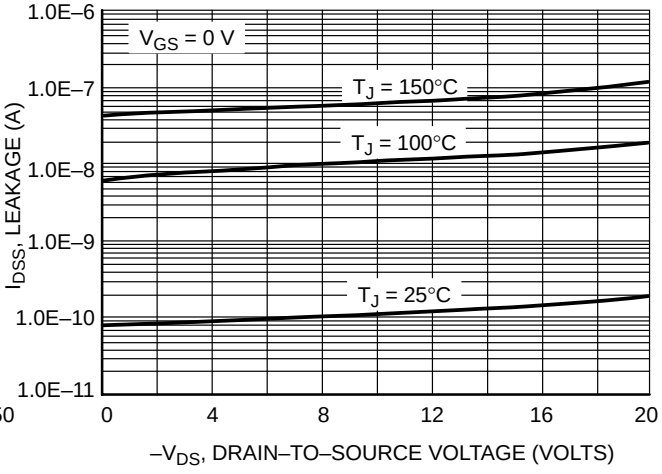


Figure 6. Drain–to–Source Leakage Current vs. Voltage

TYPICAL ELECTRICAL CHARACTERISTICS

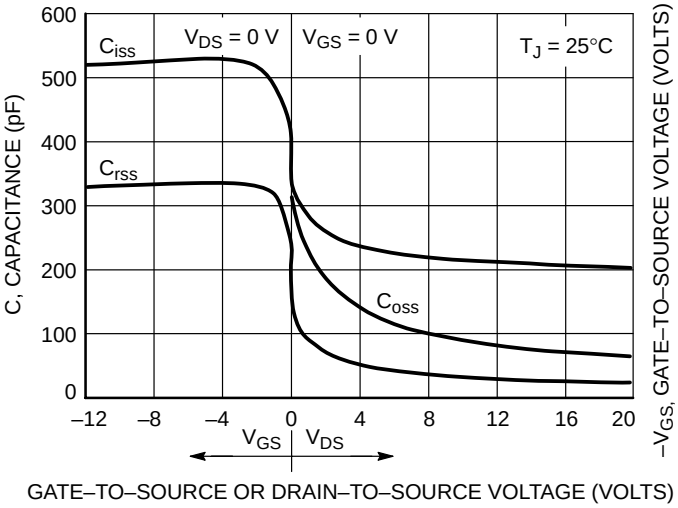


Figure 7. Capacitance Variation

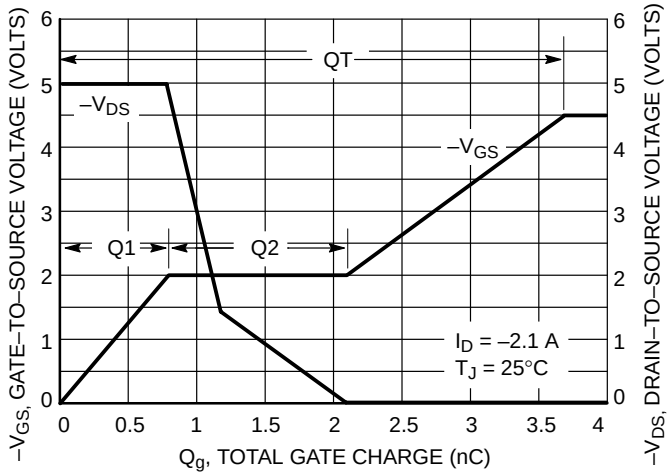


Figure 8. Gate–to–Source and Drain–to–Source Voltage vs. Total Charge

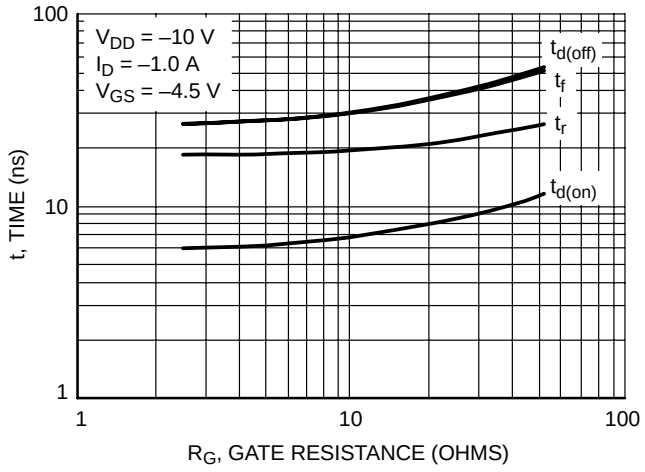


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

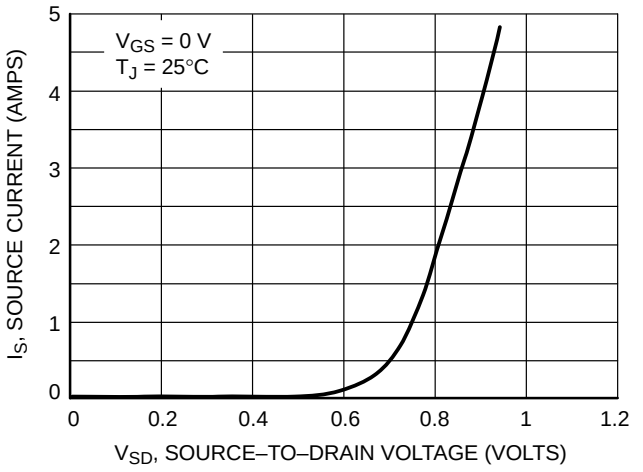


Figure 10. Diode Forward Voltage vs. Current

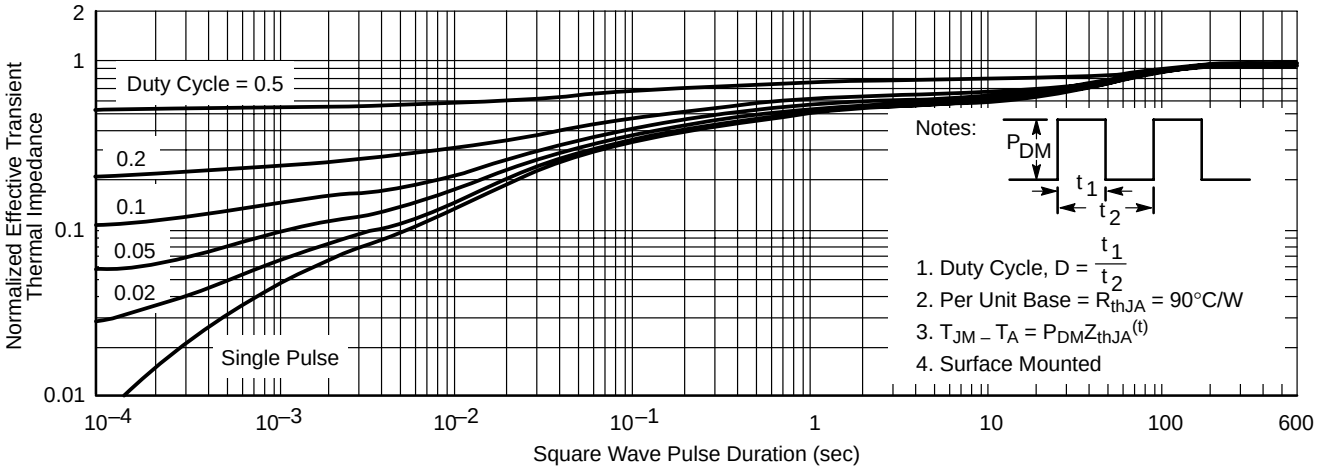


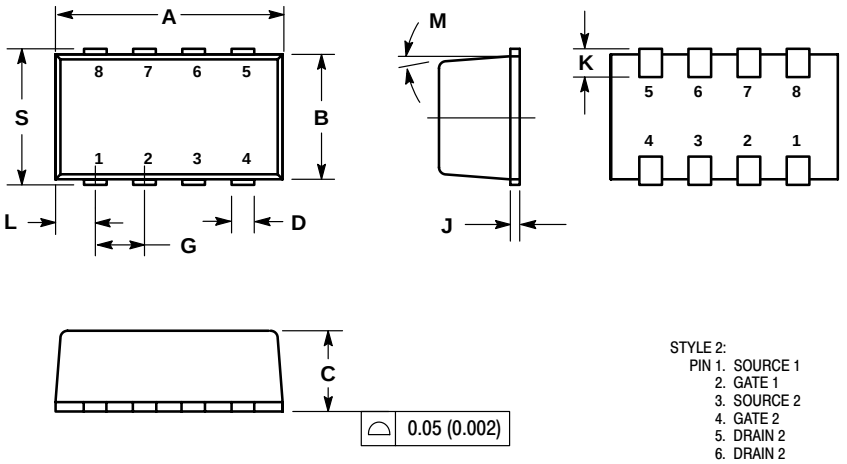
Figure 11. Normalized Thermal Transient Impedance, Junction–to–Ambient

Notes

Notes

PACKAGE DIMENSIONS

ChipFET
CASE 1206A–03
ISSUE D



STYLE 2:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MOLD GATE BURRS SHALL NOT EXCEED 0.13 MM PER SIDE.
4. LEADFRAME TO MOLDED BODY OFFSET IN HORIZONTAL AND VERTICAL SHALL NOT EXCEED 0.08 MM.
5. DIMENSIONS A AND B EXCLUSIVE OF MOLD GATE BURRS.
6. NO MOLD FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.
7. 1206A–01 AND 1206A–02 OBSOLETE. NEW STANDARD IS 1206A–03.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	2.95	3.10	0.116	0.122
B	1.55	1.70	0.061	0.067
C	1.00	1.10	0.039	0.043
D	0.25	0.35	0.010	0.014
G	0.65 BSC		0.025 BSC	
J	0.10	0.20	0.004	0.008
K	0.28	0.42	0.011	0.017
L	0.55 BSC		0.022 BSC	
M	5 ° NOM		5 ° NOM	
S	1.80	2.00	0.072	0.080

ChipFET is a trademark of Vishay Siliconix.

PUBLICATION ORDERING INFORMATION

Literature Fulfillment:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada
Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada
Email: ONlit@hibbertco.com

N. American Technical Support: 800–282–9855 Toll Free USA/Canada

JAPAN: ON Semiconductor, Japan Customer Focus Center
4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–0031
Phone: 81–3–5740–2700
Email: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local
Sales Representative.